

## 9.0 ASCENT DC ELECTRICAL CHARACTERISTICS

( $V_{DD} = 5.0V \pm 10\%$ ;  $V_{SS} = 0V$ <sup>1</sup>;  $-55^{\circ}C < T_c < +125^{\circ}C$ )

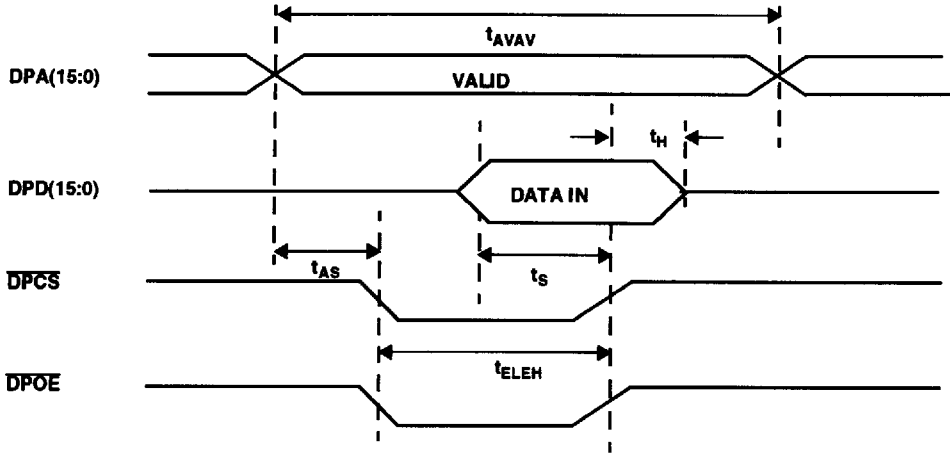
SYMBOL	PARAMETER	CONDITION	MIN	MAX	UNIT
$V_{IL}$	Low-level input voltage			$.3V_{DD}$	V
$V_{IH}$	High-level input voltage		$.7V_{DD}$		V
$I_{IN}$	Input leakage current Inputs without pull-up resistors Inputs with pull-up resistors Inputs with pull-up resistors	$V_{IN} = V_{DD}$ or $V_{SS}$ $V_{IN} = V_{DD}$ $V_{IN} = V_{SS}$	-1 -10 -100	+1 +10 -15	$\mu A$
$V_{OL}$	CMOS low-level output voltage Open drain outputs All other outputs	$I_{OL} = 8.0mA$ $I_{OL} = 1.0\mu A$		.4 0.05	V
$V_{OH}$	CMOS high-level output voltage Open drain outputs All other outputs	N/A $I_{OH} = -1.0\mu A$	N/A $V_{DD}-0.05$		V
$I_{OZ}$	Three-state output leakage current Open drain outputs All other outputs	$I_O = V_{DD}$ or $V_{SS}$ $I_O = V_{DD}$ or $V_{SS}$	-20 -10	+20 +10	$\mu A$
$I_{OS}$	Short-circuit output current <sup>2, 3</sup> All outputs All outputs	$V_{DD} = 5.5V, V_O = 0V$ $V_{DD} = 5.5V, V_O = V_{DD}$	-100	+100	mA
$C_{IN}$	Input capacitance <sup>4</sup>	$f = 1MHz @ 0V$		25	pF
$C_{OUT}$	Output capacitance <sup>4</sup> Single-drive buffer	$f = 1MHz @ 0V$		25	pF
$C_{IO}$	Bidirectional capacitance <sup>4</sup>	$f = 1MHz @ 0V$		25	pF
$Q_{IDD}$	Quiescent current <sup>5</sup>	$f = 0MHz$		375	mA
$S_{IDD}$	Standby operating current <sup>6</sup>	$f = 40MHz$		375	mA

### Notes:

1. Maximum allowable relative shift = 50mV.
2. Supplied as a design limit but not guaranteed or tested.
3. Not more than one output may be shorted at a time for maximum duration of one second.
4. Capacitance measured for initial qualification or design changes which may affect the value.
5. All inputs tied to  $V_{DD}$ .
6. Guaranteed by characterization, but not tested.

## 10.0 ASCENT AC ELECTRICAL CHARACTERISTICS<sup>1</sup>

( $f = 40\text{MHz} \pm 0.01\%$ , Duty Cycle  $50\% \pm 10\%$ )

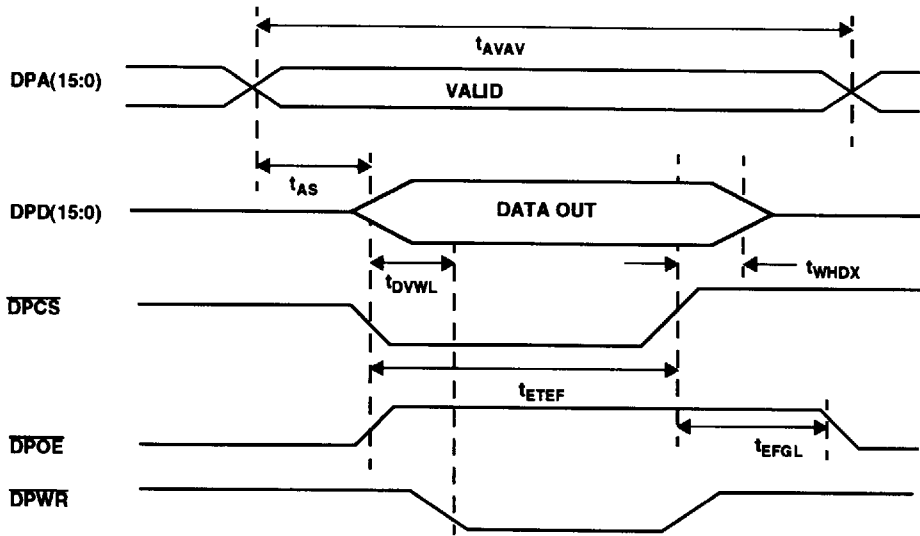


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AVAV}$	Read cycle time	240	--	ns
$t_{AS}$	Address setup time to DPCS and DPOE	-10	15	ns
$t_S$	Data valid setup to DPCS, DPOE inactive	20	--	ns
$t_H$	Data valid hold time from DPCS, DPOE inactive	10	--	ns
$t_{ELEH}$	DPCS, DPOE low width	185	--	ns

### Notes:

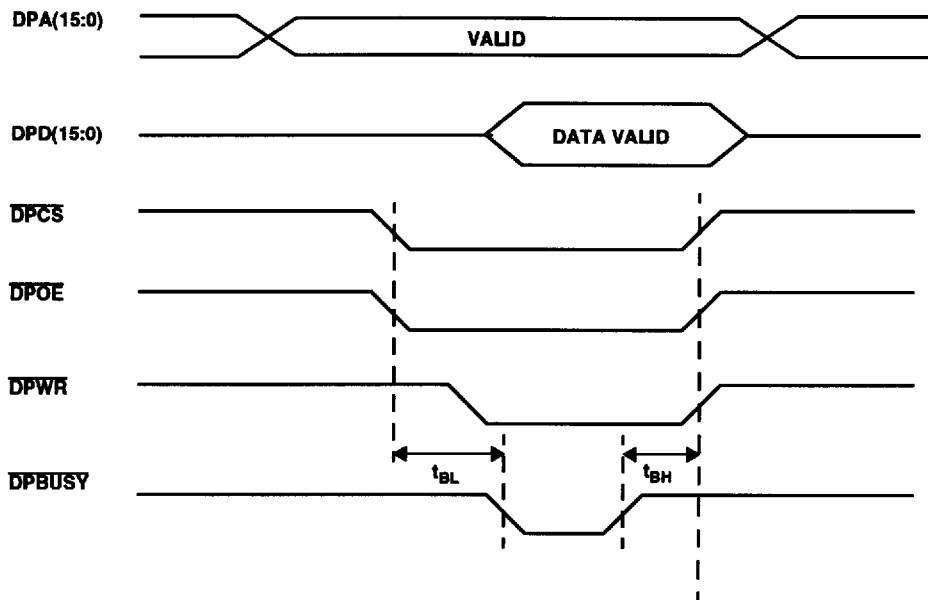
1. Guaranteed by characterization, but not tested.

Figure 10-1. Dual-port RAM Read Timing Diagram



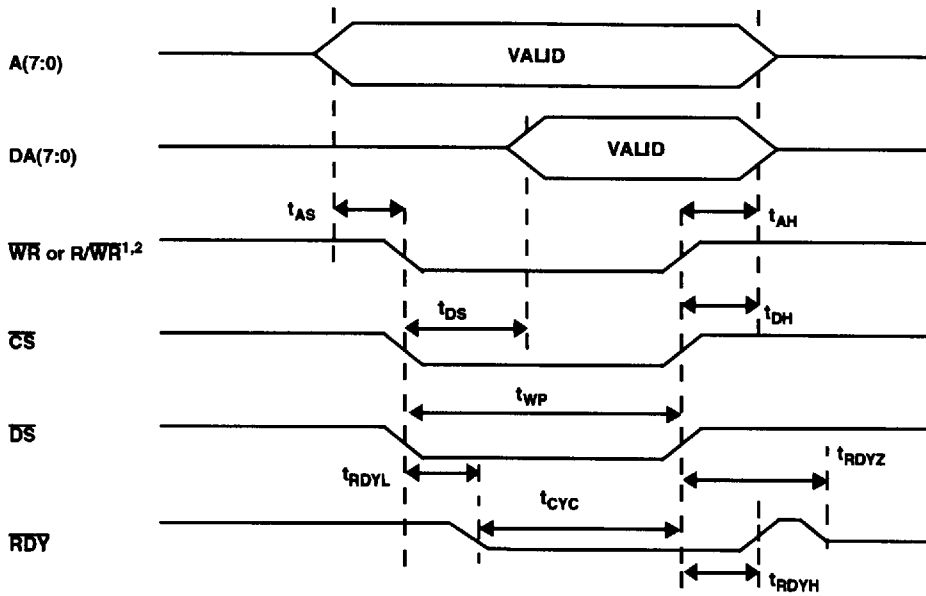
SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AVAV}$	Write cycle time	240	--	ns
$t_{AS}$	Address setup time to DPCS , DPOE and DPD(15:0) valid	-10	15	ns
$t_{DVWL}$	Data valid to DPWR active	40	55	ns
$t_{WHDX}$	DPWR high to data invalid	0	--	ns
$t_{ETEF}$	DPCS low width	185	--	ns
$t_{EGL}$	DPCS high to DPOE low	45	--	ns

Figure 10-2. Dual-port RAM Write Timing Diagram



SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{BL}$	Busy delay from DPCS	--	35	ns
$t_{BH}$	Cycle hold after Busy inactive	140	215	ns

Figure 10-3. Dual-port RAM Busy Timing

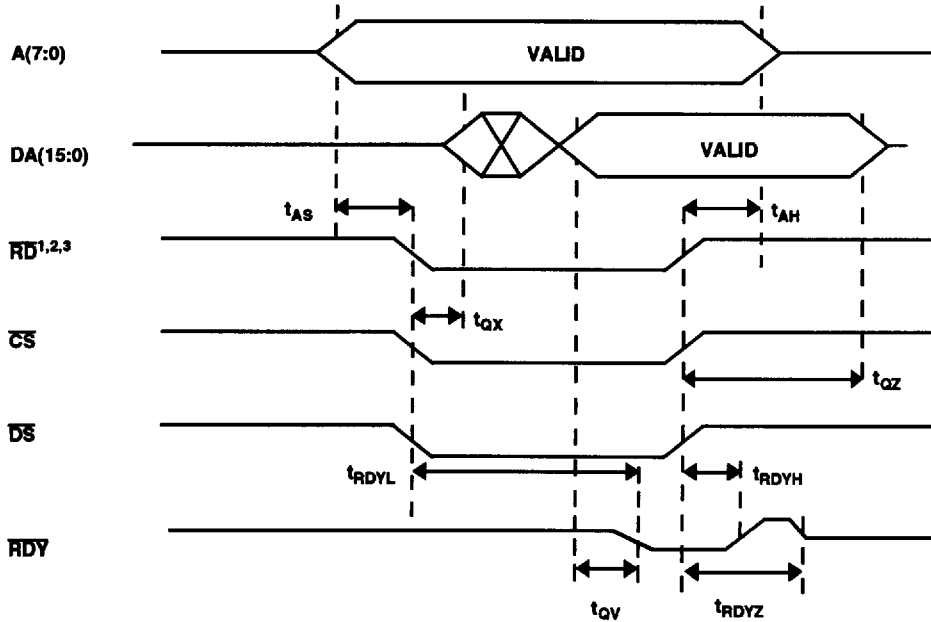


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AS}$	Address setup time	0	--	ns
$t_{DS}$	Data setup time	--	65	ns
$t_{WP}$	Write pulse width <sup>3</sup>	120	--	ns
$t_{AH}$	Address hold time	0	--	ns
$t_{DH}$	Data hold time	0	--	ns
$t_{RDYL}$	RDY low time	--	120	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns
$t_{CYC}$	Minimum cycle time	0	--	ns

**Notes:**

1. A cycle begins on the latter falling edge of  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$ .
2. A cycle ends on the rising edge of either  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$ .
3. For applications not using RDY signal.

**Figure 10-4. Non-Multiplexed Memory/Register Write (8 Bit)**

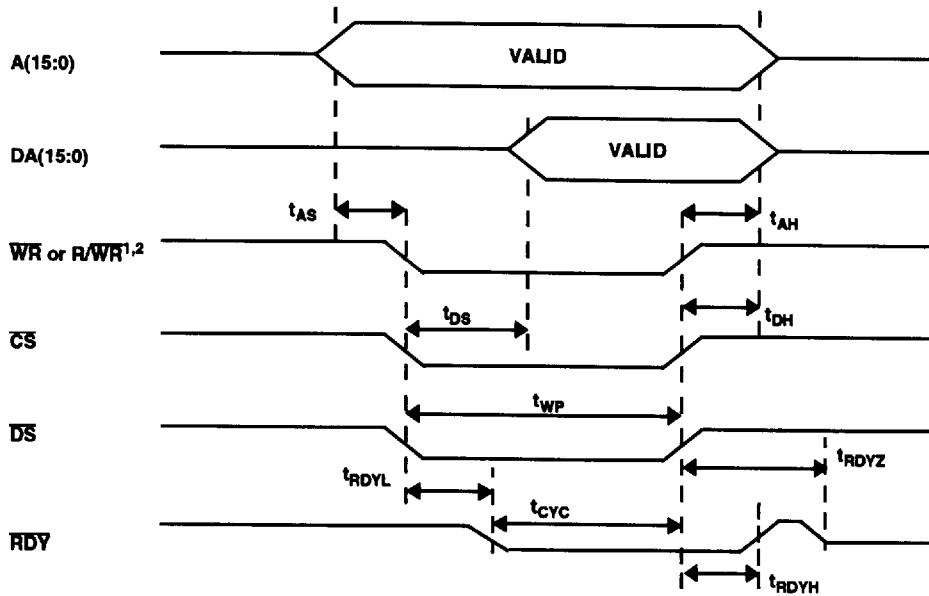


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AS}$	Address setup time	0	--	ns
$t_{QX}$	Data low Z	0	35	ns
$t_{AH}$	Address hold time	0	--	ns
$t_{QV}$	Data valid to RDY low	35	--	ns
$t_{QZ}$	Data high Z	0	25	ns
$t_{RDYL}$	RDY low time	--	350	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns

**Note:**

1. A cycle begins on the latter falling edge of  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{RD}$ .
2. A cycle ends on the rising edge of either  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{RD}$ .
3. When using  $R/\overline{WR}$  as an input signal tie  $\overline{RD}$  to a logical "1". During the read cycle  $R/\overline{WR}$  remains a logical "1".

**Figure 10-5. Non-Multiplexed Memory/Register Read (8 Bit)**

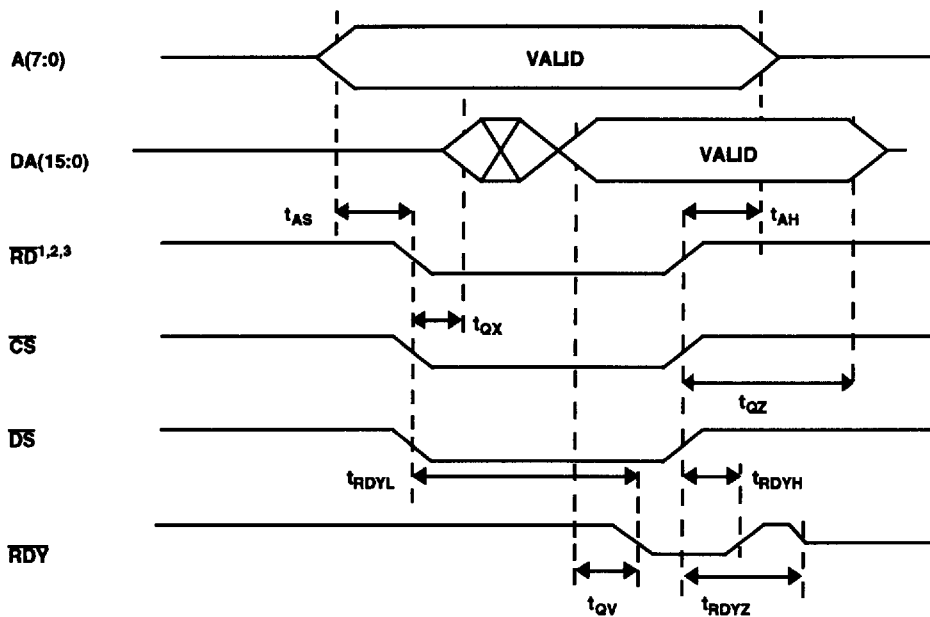


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AS}$	Address setup time	0	--	ns
$t_{DS}$	Data setup time	--	65	ns
$t_{WP}$	Write pulse width <sup>3</sup>	120	--	ns
$t_{AH}$	Address hold time	0	--	ns
$t_{DH}$	Data hold time	0	--	ns
$t_{RDYL}$	RDY low time	--	120	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns
$t_{CYC}$	Minimum cycle time	0	--	ns

**Notes:**

1. A cycle begins on the latter falling edge of CS, DS and WR or R/W.
2. A cycle ends on the rising edge of either CS, DS and WR or R/W.
3. For applications not using RDY signal.

**Figure 10-6. Non-Multiplexed Memory/Register Write (16 Bit)**



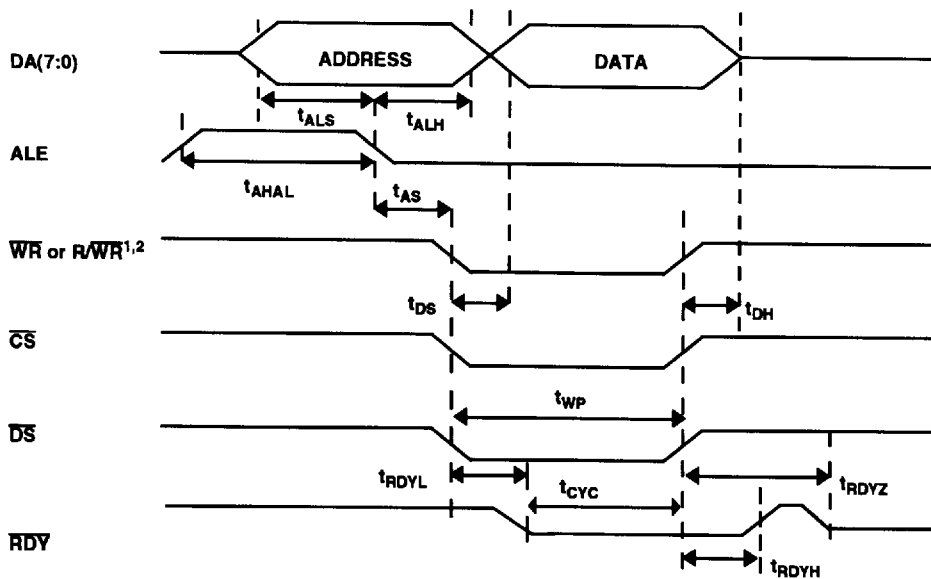
SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AS}$	Address setup time	0	--	ns
$t_{QX}$	Data low Z	0	35	ns
$t_{AH}$	Address hold time	0	--	ns
$t_{QV}$	Data valid to RDY low	35	--	ns
$t_{QZ}$	Data high Z	0	25	ns
$t_{RDYL}$	RDY low time	--	350	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns

**Notes:**

1. A cycle begins on the latter falling edge of CS, DS and RD.
2. A cycle ends on the rising edge of either CS, DS and RD.
3. When using R/WK as an input signal tie RD to a logical "1". During the read cycle R/WK remains a logical "1".

**Figure 10-7. Non-Multiplexed Memory/Register Read (16 Bit)**



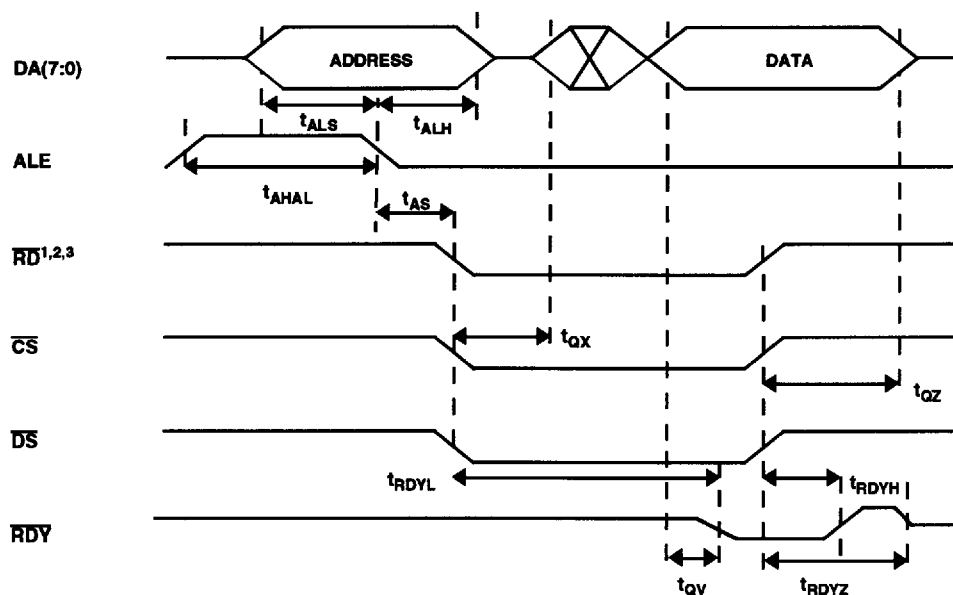


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AHAL}$	ALE pulse width	35	--	ns
$t_{ALS}$	Address latch setup time	10	--	ns
$t_{ALH}$	Address latch hold time	10	--	ns
$t_{AS}$	Address setup time	0	--	ns
$t_{DS}$	Data setup time	--	65	ns
$t_{WP}$	Write pulse width <sup>3</sup>	120	--	ns
$t_{DH}$	Data hold time	0	--	ns
$t_{RDYL}$	$\overline{RDY}$ low time	--	120	ns
$t_{RDYH}$	$\overline{RDY}$ high time	--	25	ns
$t_{RDYZ}$	$\overline{RDY}$ high Z	--	120	ns
$t_{CYC}$	Minimum cycle time	0	--	ns

**Notes:**

1. A cycle begins on the latter falling edge of  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$ .
2. A cycle ends on the rising edge of either  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$ .
3. For applications not using  $\overline{RDY}$  signal.

**Figure 10-8. Multiplexed Memory/Register Write (8 Bit)**

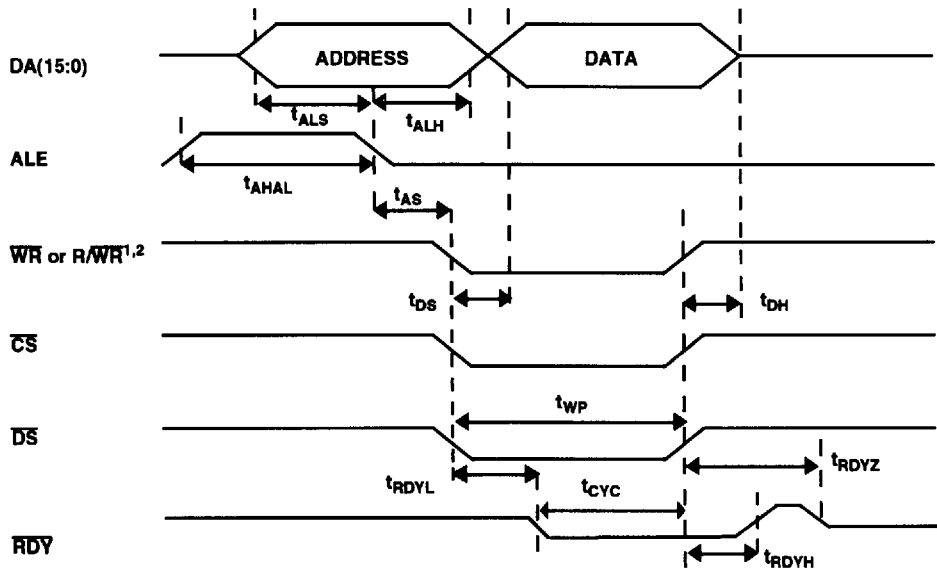


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AHAL}$	ALE pulse width	35	--	ns
$t_{ALS}$	Address latch setup time	10	--	ns
$t_{ALH}$	Address latch hold time	10	--	ns
$t_{AS}$	Address setup time	0	--	ns
$t_{QX}$	Data low Z	0	10	ns
$t_{QV}$	Data valid to RDY low	35	--	ns
$t_{QZ}$	Data high Z	0	25	ns
$t_{RDYL}$	RDY low time	--	350	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns

**Notes:**

1. A cycle begins on the latter falling edge of CS, DS and RD.
2. A cycle ends on the rising edge of either CS, DS and RD.
3. When using R/WR as an input signal tie RD to a logical "1". During the read cycle R/WR remains a logical "1".

**Figure 10-9. Multiplexed Memory/Register Read (8 Bit)**

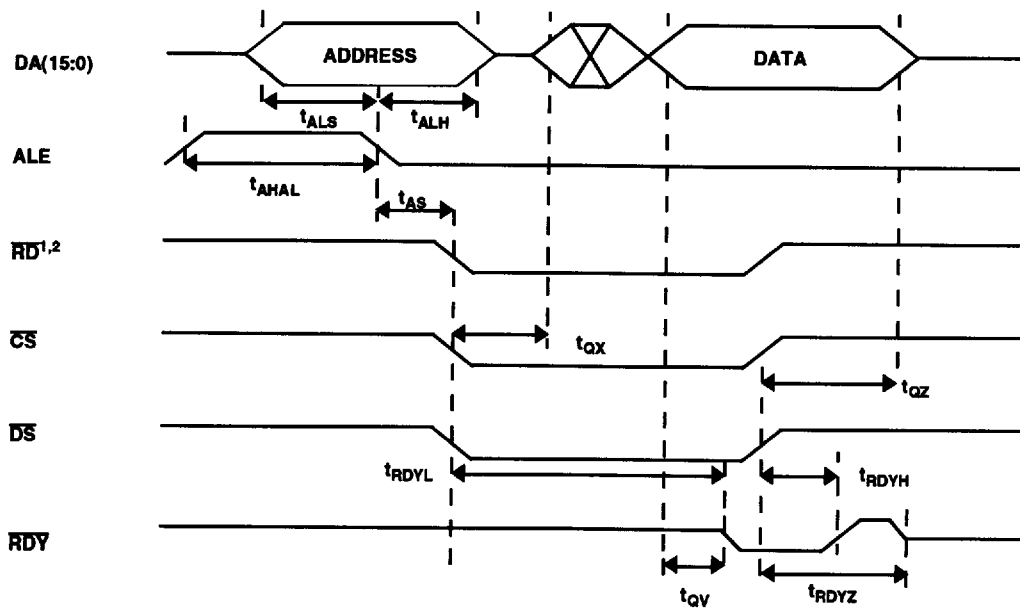


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AHAL}$	ALE pulse width	35	--	ns
$t_{ALS}$	Address latch setup time	10	--	ns
$t_{ALH}$	Address latch hold time	10	--	ns
$t_{AS}$	Address setup time	0	--	ns
$t_{DS}$	Data setup time	--	65	ns
$t_{WP}$	Write pulse width <sup>3</sup>	120	--	ns
$t_{DH}$	Data hold time	0	--	ns
$t_{RDYL}$	$\overline{RDY}$ low time	--	120	ns
$t_{RDYH}$	$\overline{RDY}$ high time	--	25	ns
$t_{RDYZ}$	$\overline{RDY}$ high Z	--	120	ns
$t_{CYC}$	Minimum cycle time	0	--	ns

**Notes:**

1. A cycle begins on the latter falling edge of  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$
2. A cycle ends on the rising edge of either  $\overline{CS}$ ,  $\overline{DS}$  and  $\overline{WR}$  or  $\overline{R/W}$ .
3. For applications not using  $\overline{RDY}$  signal.

**Figure 10-10. Multiplexed Memory/Register Write (16 Bit)**

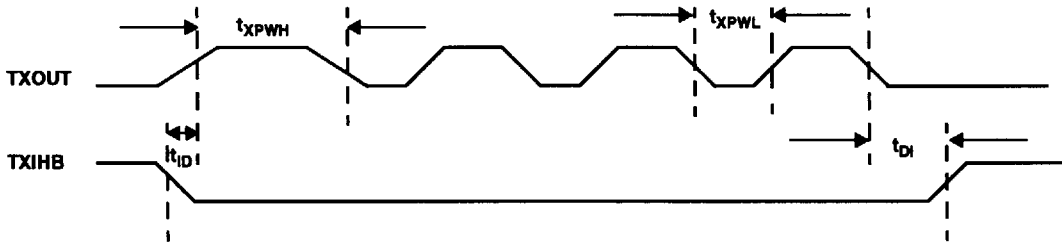


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{AHAL}$	ALE pulse width	35	--	ns
$t_{ALS}$	Address latch setup time	10	--	ns
$t_{ALH}$	Address latch hold time	10	--	ns
$t_{AS}$	Address setup time	0	--	ns
$t_{QX}$	Data low Z	0	10	ns
$t_{QV}$	Data valid to RDY low	35	--	ns
$t_{QZ}$	Data high Z	0	25	ns
$t_{RDYL}$	RDY low time	--	350	ns
$t_{RDYH}$	RDY high time	--	25	ns
$t_{RDYZ}$	RDY high Z	--	120	ns

**Notes:**

1. A cycle begins on the latter falling edge of CS, DS and RD.
2. A cycle ends on the rising edge of either CS, DS and RD

**Figure 10-11. Multiplexed Memory/Register Read (16 Bit)**

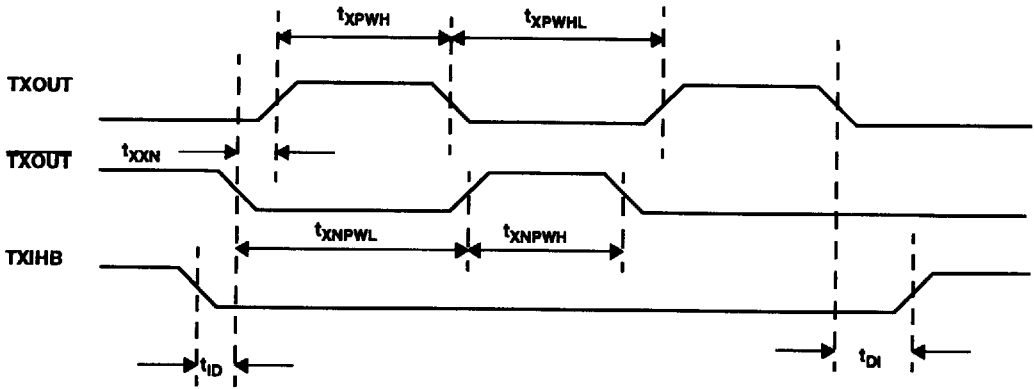


SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{XPWH}$	TXOUT pulse width high	21	--	ns
$t_{XPWL}$	TXOUT pulse width low	25	--	ns
$t_{ID}$	TXIHB inactive to first data	50	150	ns
$t_{DI}$	Last data to inhibit active <sup>1</sup>	1005	1020	ns

**Notes:**

1. TXIM set to 0.

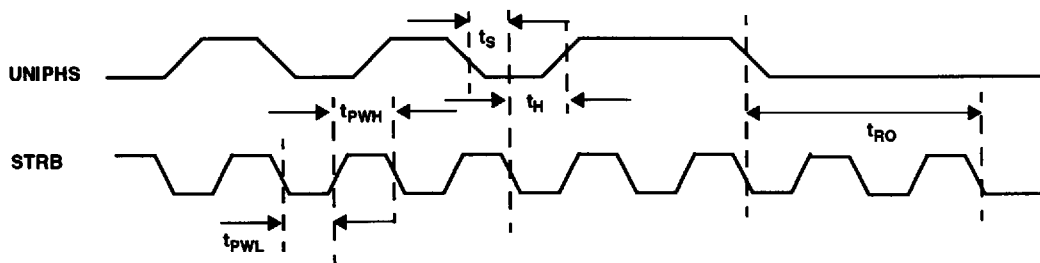
**Figure 10-12. 20Mbps Transmit Timing Diagram**



SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{XPWH}$	TXOUT pulse with high	492	--	ns
$t_{XPWHL}$	TXOUT pulse width low	498	--	ns
$t_{XKN}$	Skew TXOUT to TXOUT	-2	10	ns
$t_{XNPWH}$	TXOUT pulse width high	490	--	ns
$t_{XNPWL}$	TXOUT pulse width low	498	--	ns
$t_{ID}$	Inhibit release to first data	275	512	ns
$t_{DI}$	Last data to inhibit active <sup>1</sup>	950	1050	ns

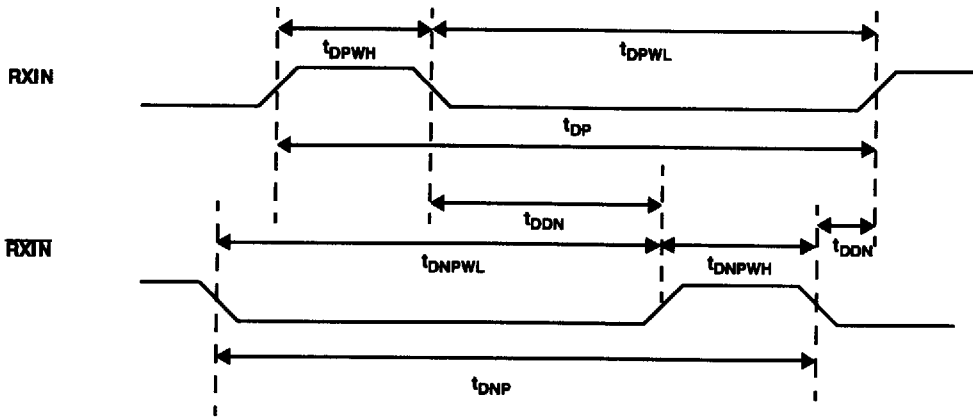
Notes:  
 1. TXIM set to 0.

Figure 10-13. 1Mbps Transmit Timing Diagram



SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_H$	UNIPHS hold from STRB $\downarrow$	5	--	ns
$t_s$	UNIPHS setup to STRB $\downarrow$	5	--	ns
$t_{pWH}$	STRB pulse width high	5	--	ns
$t_{pWL}$	STRB pulse width low	5	--	ns
$t_{RO}$	STRB run-on after data end	33	--	clocks

Figure 10-14. 20Mbps Receive Timing Diagram



SYMBOL	PARAMETER	MINIMUM	MAXIMUM	UNITS
$t_{DPWH}$	RXIN pulse width high	75	650	ns
$t_{DPWL}$	RXIN pulse width low	75	650	ns
$t_{DNPWL}$	RXIN pulse width low	75	650	ns
$t_{DNPWH}$	RXIN pulse width high	75	650	ns
$t_{DP}$	RXIN bit period	998	1002	ns
$t_{DDN}$	RXIN to RXIN delay	0	225	ns
$t_{DNP}$	RXIN bit period	998	1002	ns

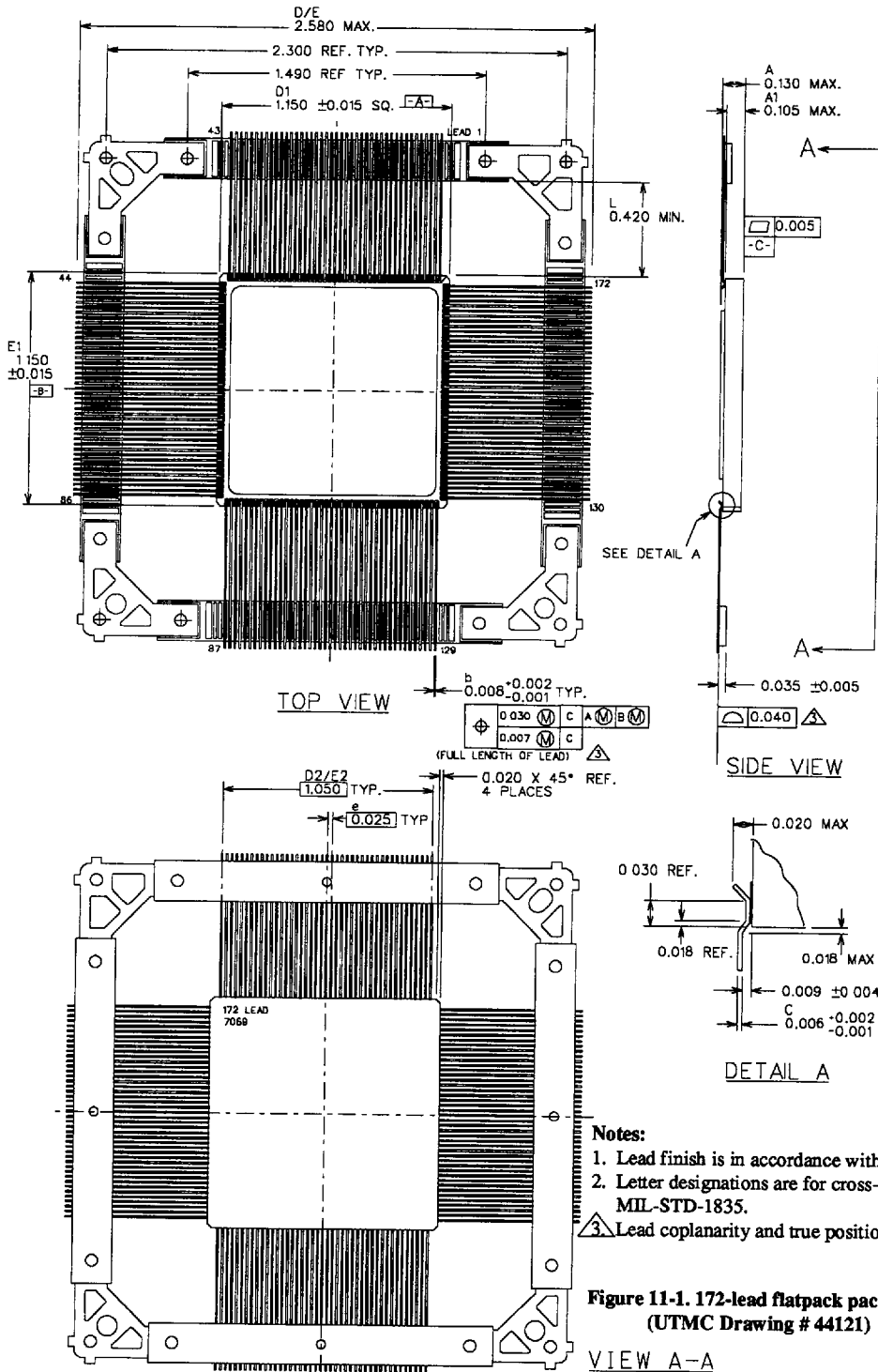
Figure 10-15. 1 Mbps Receive Timing Diagram



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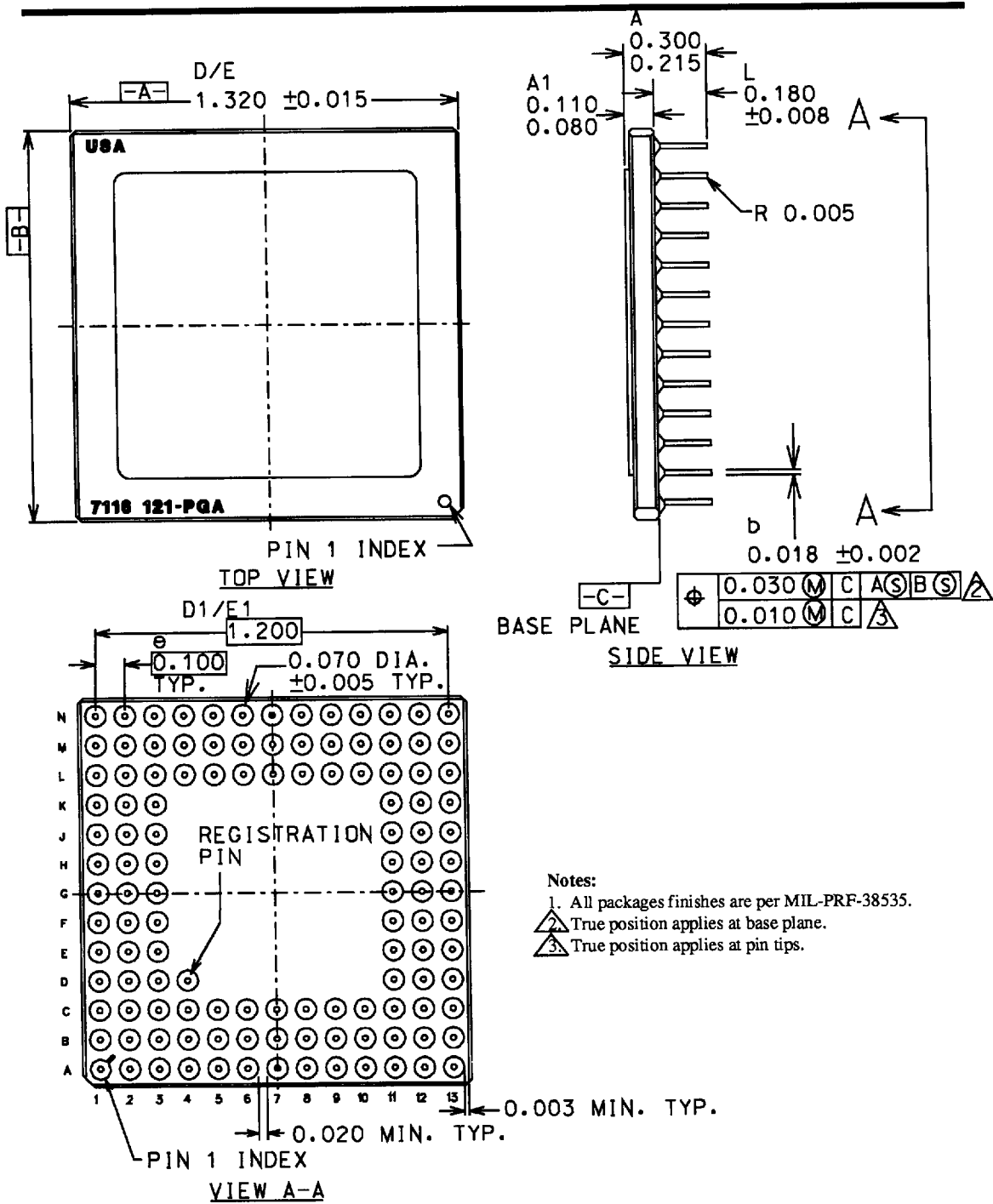
## 11.0 Packages

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- Notes:**
1. Lead finish is in accordance with MIL-PRF-38535.
  2. Letter designations are for cross-reference to MIL-STD-1835.
  3. Lead coplanarity and true position are not measured.

**Figure 11-1. 172-lead flatpack package (UTMC Drawing # 44121)**



- Notes:
- All packages finishes are per MIL-PRF-38535.
  - True position applies at base plane.
  - True position applies at pin tips.

Figure 11-2. 121-pin pingrid array package (UTMC Drawing # 44128)